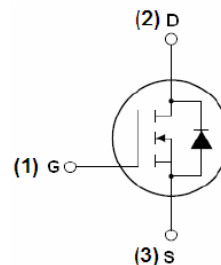


## FEATURES

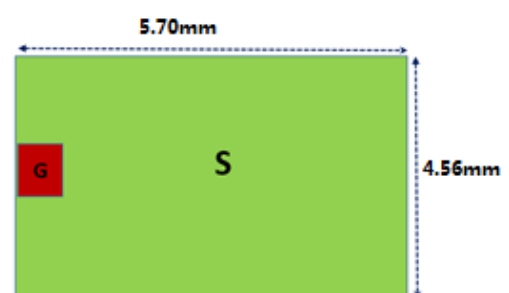
- 150V、150A\* , N-channel
- $R_{DS(on)}=7m\Omega(MAX)$
- Ultra low  $Q_{gd}$
- Fast switching



## Electrical Characteristics( $T_J=25^{\circ}C$ )

Parameter	Description	Min.	Typ.	Max.	Unit	Test Condition
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	150			V	$V_{GS}=0V, I_D=250\mu A$
$R_{DS(on)}$	Static Drain-Source On-Resistance			7	m $\Omega$	$V_{GS}=10V, I_D=75A$
$V_{GS(th)}$	Gate Threshold Voltage	2.0		4.0	V	$V_{DS}=V_{GS}, I_D=250\mu A$
$I_{DSS}$	Drain-to-Source Leakage Current			1	$\mu A$	$V_{DS}=150V, V_{GS}=0V, T_J=25^{\circ}C$
$I_{GSS}$	Gate-Body Leakage Current			$\pm 100$	nA	$V_{GS}=\pm 20V$
$V_{SD}$	Body Diode Voltage			1.5	V	$V_{GS}=0V, I_{SD}=150A$
$T_J, T_{stg}$	Operating and Storage Temperature Range	-55~+150			$^{\circ}C$	

## Mechanical Date

Die Size	5700×4560	$\mu m^2$	
Gate Pad Size	280×400		
Source Pad Size	No Passivation		
Scribe Line Size	80	$\mu m$	
Wafer Diameter	200	mm	
Wafer Thickness	200	$\mu m$	
Passivation Frontside	No Passivation	---	
Source Metallization	AlCu , 4.0	$\mu m$	
Drain Metallization	Ti-Ni-Ag 1K-2K-10K	A	
Reject Ink Dot Size	0.51	mm	
Recommended Storage Environment	Store in original container, in desiccated nitrogen, with no contamination		

\* Electrical characteristics are reported for the reference packaged part (TO-220/263) and cannot be guaranteed in die sales form.

Variations in customer packaging materials, dimensions and processes may affect parametric performance.